

This listing of claims will replace all prior versions of claims in the application.

Claims 1-10. (cancelled).

Claim. 11. (currently amended) A method for providing a photoresist relief image, comprising:

- (a) applying a coating layer of a ~~positive-acting~~ photoresist composition onto a substrate, the photoresist composition comprising a silsesquioxane resin ~~that comprises three or more distinct repeat units, the repeat units~~ comprising hexafluoropropylalcohol groups and photoacid-labile groups;
  - (b) exposing the photoresist composition to patterned activating radiation having a wavelength of 193 nm;
  - (c) developing the exposed photoresist layer to provide a photoresist relief image;
- wherein the exposing of the photoresist does not result in a detectable output of Si species at a concentration of  $1 \times 10^{13}$  molecules/cm<sup>2</sup> or greater.

Claim 12. (previously presented) The method of claim 11 wherein the photoresist composition is coated over an organic polymer layer.

Claim 13. (cancelled)

Claim 14. (previously presented) The method of claim 11 wherein the resin is completely free of aromatic groups.

Claim 15. (previously presented) The method of claim 11 further comprising thermally treating the applied photoresist composition layer and then thermally treated photoresist layer is exposed.

Claim 16. (previously presented) The method of claim 15 wherein after exposure the photoresist composition layer is thermally treated and then developed.

Claim 17. (new) The method of claim 11 wherein the resin comprises acetal groups.

Claim 18. (new) The photoresist composition of claim 11 wherein the resin comprises four or more distinct repeat units.

Claim 19. (new) The method of claim 18 wherein the resin comprises acetal groups.